



M

E

 $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	50	A
	$I_{D@TC=75}$	38	A
	$I_{D@TC=100}$	31.5	A
Pulsed Drain Current	I_{DM}	150	A
Total Power Dissipation	$P_D@TC=25$	54	W
Total Power Dissipation	$P_D@TA=25$	2	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	

Single Pulse Avalanche Energy



Note:

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Fig.1 Gate-Charge Characteristics

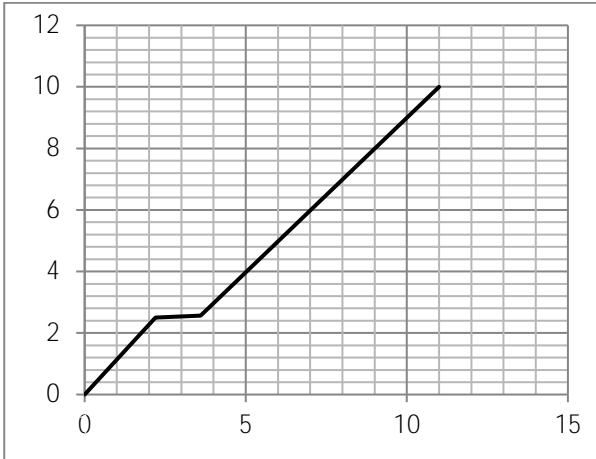


Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

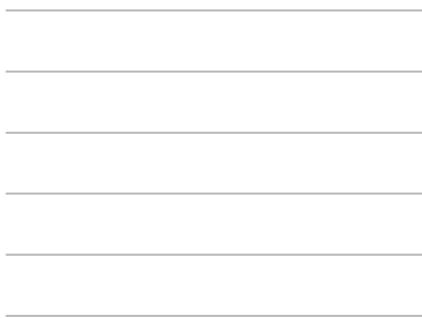


Fig.4 Typical output Characteristics

Fig.5 Threshold Voltage V.S Junction Temperature Fig.6 Resistance V.S Drain Current

H (TO-252)

Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

